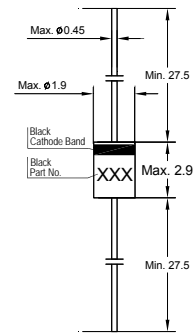


# 1SS176

## Silicon Epitaxial Planar Switching Diode

### Applications

- High-speed switching



Glass Case DO-34  
Dimensions in mm

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Peak Reverse Voltage	$V_{RM}$	35	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Forward Voltage	$I_F$	300	mA
Surge Forward Current at $t = 1\text{ s}$	$I_{FSM}$	1	A
Junction Temperature	$T_j$	175	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 175	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	$V_F$	1.2	V
Reverse Current at $V_R = 30\text{ V}$	$I_R$	0.5	$\mu\text{A}$
Capacitance at $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_{tot}$	3	pF
Reverse Recovery Time at $I_F = 100\text{ mA}$ , $V_R = 6\text{ V}$ , $R_L = 100\text{ }\Omega$	$t_{rr}$	4	ns

